

### **ABSTRACT**

The invention is an apparatus and a method of manufacturing a structure. The method includes the step of patterning a layer to include a line and space pattern. A space of the line and space pattern in a first region includes a first critical dimension less than achievable at a resolution limit of lithography. A line of the line and space pattern in a second region includes a second critical dimension achievable at a resolution limit of lithography. A sidewall spacer is formed on a line from a masking layer used in the formation of the structure. The method uses one critical masking step and two non-critical masking steps.

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